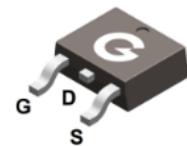
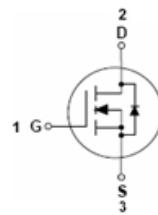


### Features

- Low power loss by high speed switching and low on-resistance
- Excellent thermal behavior
- Product validation acc. JEDEC Standard
- RoHS compliant with Halogen-free

HF



TO-252

### Mechanical Data

- Case: TO-252
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

### Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
SJM60R600XD	TO-252	80 pcs / Tube & 2500 pcs / Tape & Reel	SJM60R600XD

### Maximum Ratings (@ $T_c = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	600	V
Gate-to-Source Voltage	$V_{GSS}$	$\pm 30$	V
Continuous Drain Current ( $T_c = 25^\circ\text{C}$ )	$I_D$	8	A
Continuous Drain Current ( $T_c = 100^\circ\text{C}$ )		5	A
Pulsed Drain Current ( $t_p = 10\mu\text{s}$ , $T_c = 25^\circ\text{C}$ )	$I_{DM}$	32	A
Single Pulse Avalanche Energy <sup>3</sup>	$E_{AS}$	200	mJ
Power Dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	63	W
Operating Junction Temperature Range	$T_J$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{JC}$	-	-	2	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction-to-Air <sup>*1</sup>	$R_{JA}$	-	-	62	$^\circ\text{C}/\text{W}$



Electrical Characteristics (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu\text{A}$	600	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$R_{DS(ON)}$	Drain-Source On-resistance <sup>*2</sup>	$V_{GS} = 10V, I_D = 4A$	-	0.45	0.6	$\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	3.3	4.5	V
$R_G$	Gate Resistance	$V_{GS} = 0V, f = 1\text{MHz}$	-	12	-	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 40V$ $f = 250\text{kHz}$	-	408	-	pF
$C_{oss}$	Output Capacitance		-	88	-	
$C_{rss}$	Reverse Transfer Capacitance		-	6.5	-	
<b>Switching Characteristics</b>						
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD} = 480V$ $V_{GS} = 15V$ $I_D = 4A$ $R_G = 3.3\Omega$	-	25	-	ns
$t_r$	Turn-on Rise Time		-	33	-	
$t_{d(OFF)}$	Turn-Off Delay Time		-	40	-	
$t_f$	Turn-Off Fall Time		-	66	-	
$Q_G$	Total Gate-Charge	$V_{DD} = 480V$ $V_{GS} = 10V$ $I_D = 4A$	-	16.4	-	nC
$Q_{GS}$	Gate to Source Charge		-	2.3	-	
$Q_{GD}$	Gate to Drain (Miller) Charge		-	9.2	-	
<b>Source-Drain Diode Characteristics</b>						
$V_{SD}$	Diode Forward Voltage <sup>*2</sup>	$I_{SD} = 4A, V_{GS} = 0V$	-	0.82	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 4A, V_R = 400V$ $dI/dt = 100A/\mu\text{s}$	-	230	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	1.7	-	$\mu\text{C}$

Notes:

1. The data tested by surface mounted on a minimum recommended FR-4 board
2. The data tested by pulsed, pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$
3. The  $E_{AS}$  data shows Max. rating. The test condition is  $V_{DD} = 100V, V_{GS} = 15V, L = 50\text{mH}$

### Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

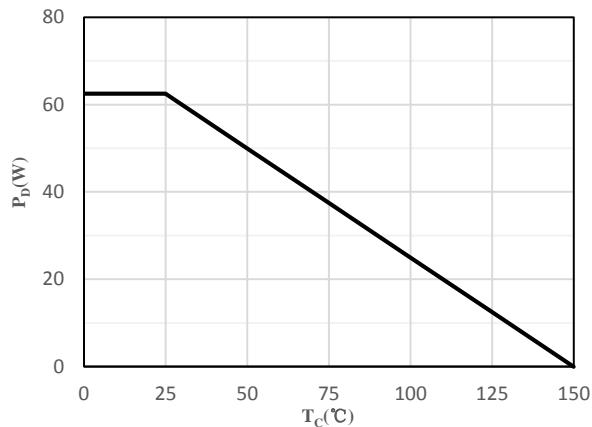


Fig 1 Power Dissipation

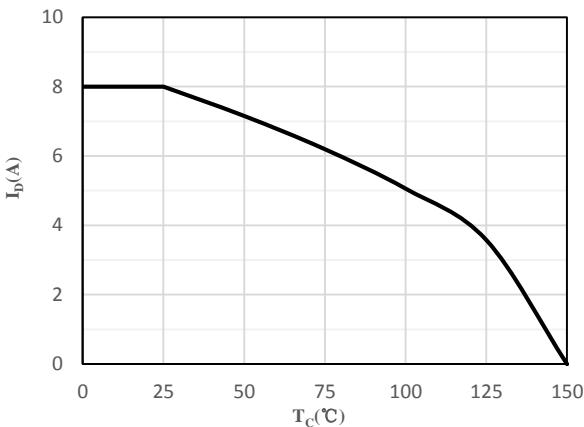


Fig 2 Drain Current

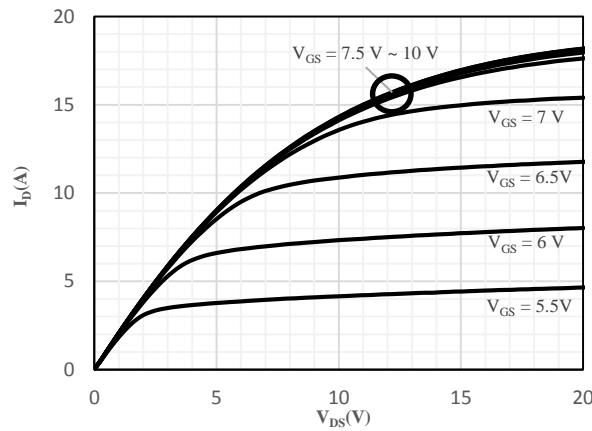


Fig 3 Typical Output Characteristics

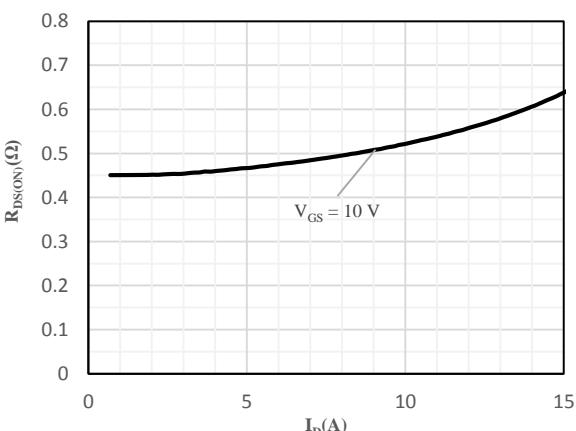


Fig 4 On-Resistance vs. Drain Current

and Gate Voltage

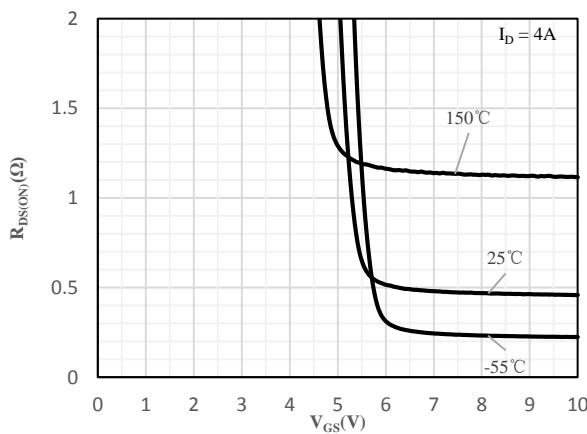


Fig 5 On-Resistance vs. Gate-Source Voltage

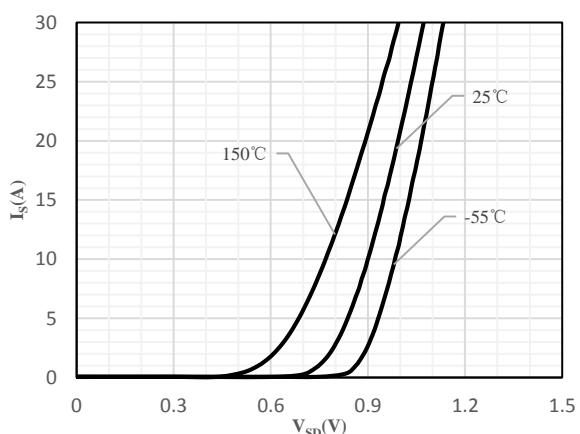
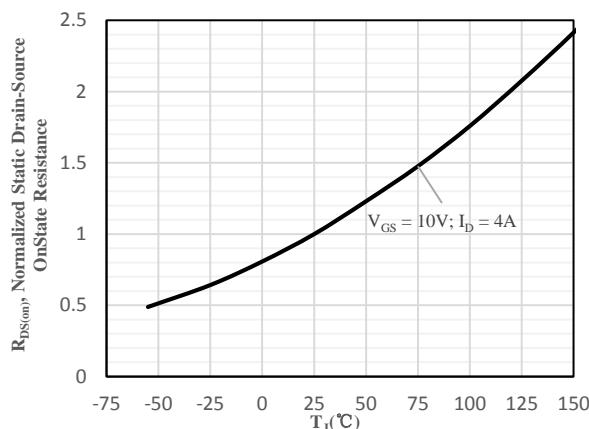
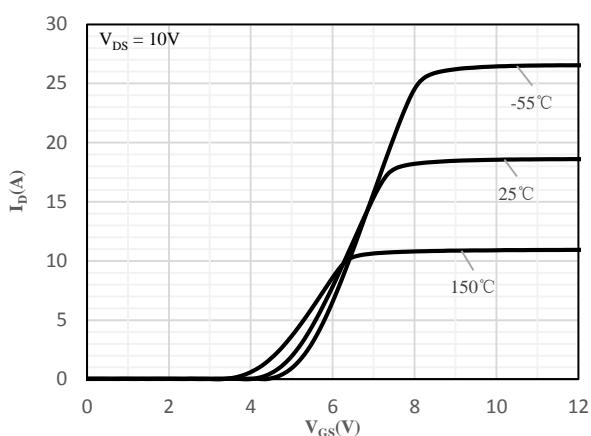


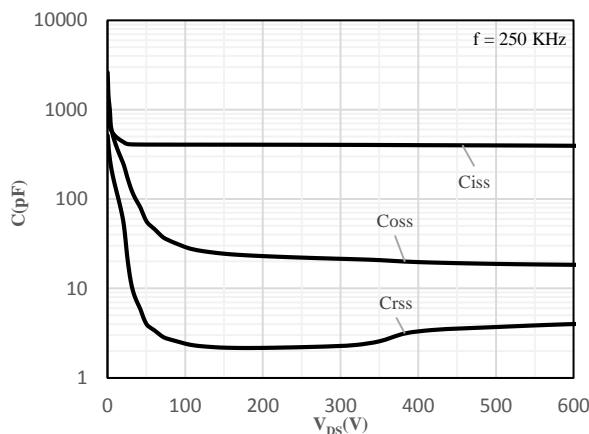
Fig 6 Body-Diode Characteristics



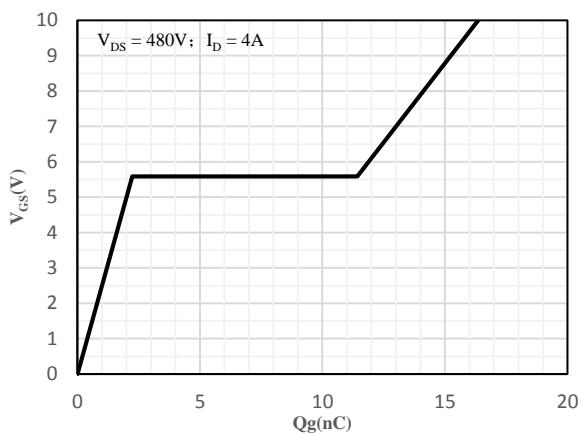
**Fig 7 Normalized On-Resistance vs. Junction Temperature**



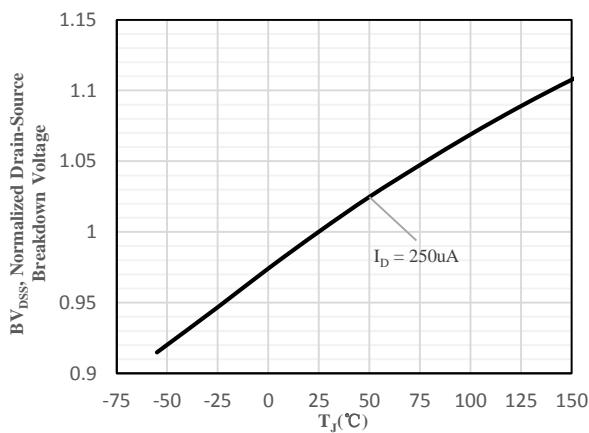
**Fig 8 Transfer Characteristics**



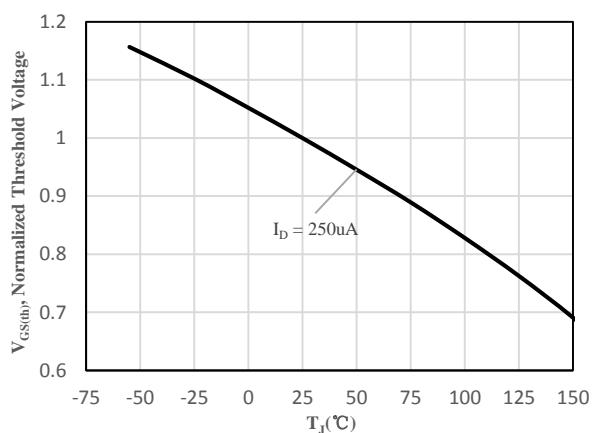
**Fig 9 Capacitance Characteristics**



**Fig 10 Gate-Charge Characteristics**



**Fig 11 Normalized Breakdown Voltage vs. Junction Temperature**



**Fig 12 Normalized V<sub>Gs(th)</sub> vs. Junction Temperature**

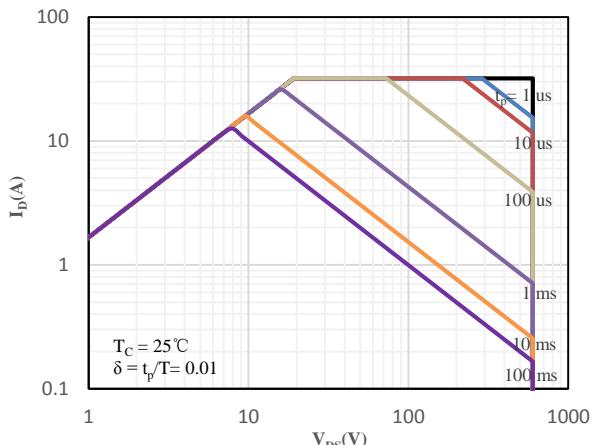


Fig 13 Safe Operation Area

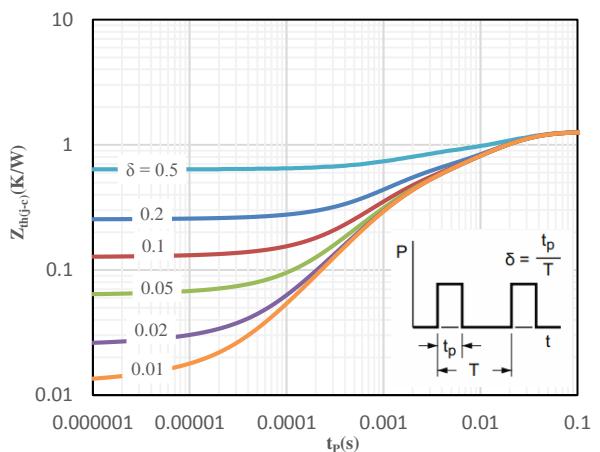
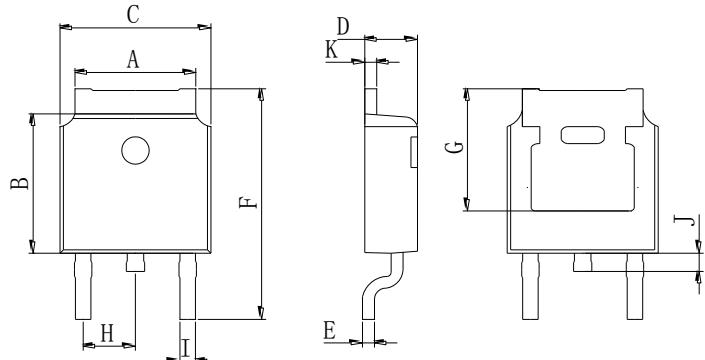


Fig 14 Maximum transient thermal impedance



**Package Outline Dimensions** (Unit: mm)



TO-252		
Dimension	Min.	Max.
A	5.05	5.65
B	5.80	6.40
C	6.25	6.85
D	2.20	2.40
E	0.40	0.60
F	9.71	10.31
G	5.05	5.65
H	2.10	2.50
I	0.70	0.90
J	0.50	0.70
K	0.40	0.60

**Mounting Pad Layout** (Unit: mm)

TO-252

